

SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

TED1402

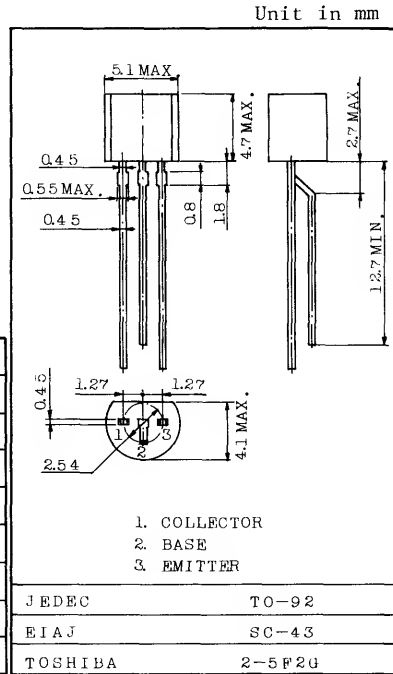
AUDIO FREQUENCY GENERAL PURPOSE AMPLIFIER APPLICATIONS.
DRIVER STAGE AMPLIFIER APPLICATIONS.

FEATURES:

- High Voltage and High Current
: $V_{CE0}=50V(\text{Min.})$, $I_C=150mA(\text{Max.})$
- Excellent h_{FE} Linearity
: $h_{FE}(I_C=0.1mA)/h_{FE}(I_C=2mA)=0.95(\text{Typ.})$
- Low Noise : $NF=1dB(\text{Typ.})$ at $f=1kHz$
- Complementary to TED1602.

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	150	mA
Base Current	I_B	50	mA
Collector Power Dissipation	P_C	400	mW
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	-65 ~ 125	°C



ELECTRICAL CHARACTERISTICS (Ta=25°C)

Weight : 0.21g

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO(1)}$	$V_{CB}=60V, I_E=0$	-	-	0.1	μA
	$I_{CBO(2)}$	$V_{CB}=60V, I_E=0, T_a=125^\circ C$	-	-	10	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_C=0$	-	-	0.1	μA
DC Current Gain	h_{FE} (Note)	$V_{CE}=5V, I_C=2mA$	110	-	810	
Collector-Emitter Saturation Voltage	$V_{CE(sat)(1)}$	$I_C=10mA, I_B=1mA$	-	0.04	0.25	V
	$V_{CE(sat)(2)}$	$I_C=100mA, I_B=5mA$	-	0.2	-	
Base-Emitter Voltage	V_{BE}	$V_{CE}=5V, I_C=1mA$	0.53	0.60	0.68	V
Transition Frequency	f_T	$V_{CE}=10V, I_E=-1mA$	-	175	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$	-	1.9	-	pF
Noise Figure	NF(1)	$V_{CE}=5V, I_E=-0.2mA$ $R_g=2k\Omega, f=1kHz$	-	1.0	10	dB
	NF(2)	$V_{CE}=5V, I_E=-1mA$ $R_g=800\Omega, f=1MHz$	-	2.0	-	

Note : h_{FE} Classification A:110 ~ 165, B:150 ~ 225, C:202 ~ 318, D:290 ~ 450,
E:414 ~ 810

